

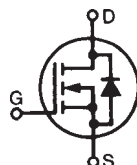
TrenchMV™ Power MOSFET

IXTC200N10T

$$\begin{aligned} V_{DSS} &= 100V \\ I_{D25} &= 101A \\ R_{DS(on)} &\leq 6.3m\Omega \end{aligned}$$

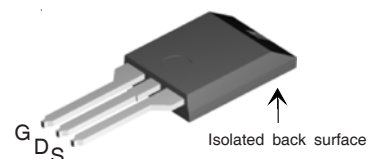
(Electrically Isolated Back Surface)

N-Channel Enhancement Mode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	100	V
V_{DGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GS} = 1M\Omega$	100	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	101	A
I_{LRMS}	Lead Current Limit, RMS	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	500	A
I_A	$T_C = 25^\circ\text{C}$	40	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
P_D	$T_C = 25^\circ\text{C}$	160	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6mm (0.062in.) from case for 10s Plastic body for 10 seconds	300 260	$^\circ\text{C}$ $^\circ\text{C}$
V_{ISOL}	50/60Hz, $t = 1$ minute, $I_{ISOL} < 1\text{mA}$, RMS	2500	V
M_d	Mounting force	11..65 / 2.5..14.6	N/lb.
Weight	ISOPLUS220	2	g

ISOPLUS220
E153432



G = Gate
S = Source
D = Drain

Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
- Isolated mounting surface
- 2500V electrical isolation

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - High Side Switch
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary - Side Switch
- High Current Switching Applications

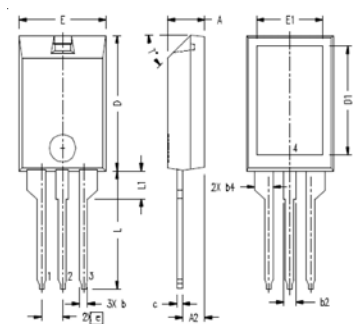
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$, Notes 1			6.3 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1	60	96	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		9400	pF
C_{oss}			1087	pF
C_{rss}			140	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{A}$ $R_G = 3.3\Omega$ (External)		35	ns
t_r			31	ns
$t_{d(off)}$			45	ns
t_f			34	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 50\text{A}$		152	nC
Q_{gs}			47	nC
Q_{gd}			47	nC
R_{thJC}				0.96°C/W
R_{thCH}		0.21		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			200 A
I_{SM}	Repetitive, Pulse width limited by T_{JM}			500 A
V_{SD}	$I_F = 50\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.0 V
t_{rr}	$I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}$		76	ns
Q_{RM}			205	nC
I_{RM}			5.4	A

ISOPLUS220 (IXTC) Outline



1. Gate 2. Drain
3. Source

Note: Bottom heatsink (Pin 4) is electrically isolated from Pins 1, 2 and 3.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100	BASIC	2.55	BASIC
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T*			42.5*	47.5*

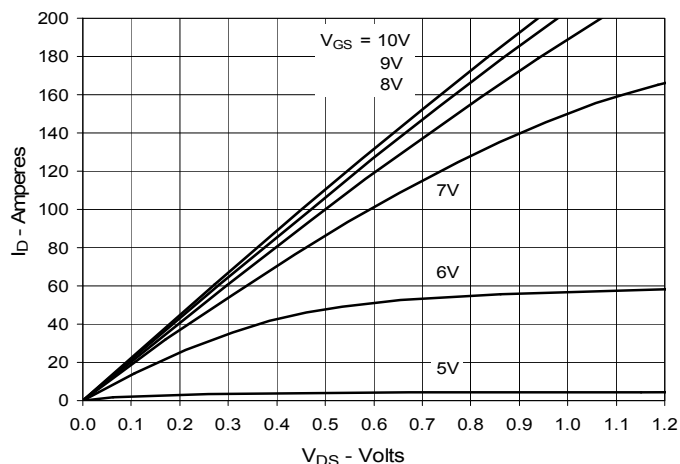
Notes: 1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

IXYS reserves the right to change limits, test conditions, and dimensions.

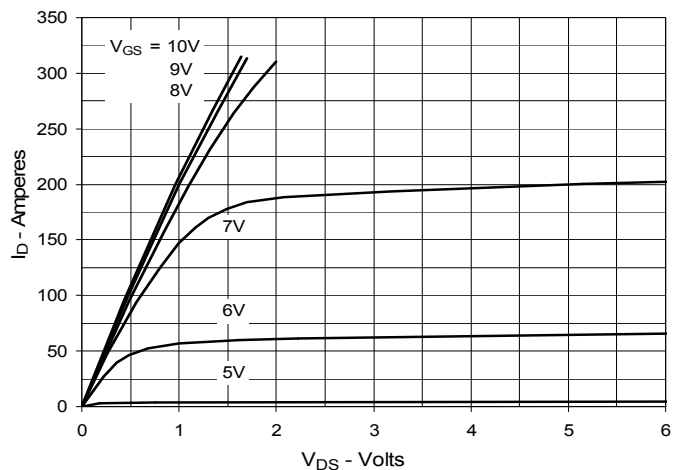
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

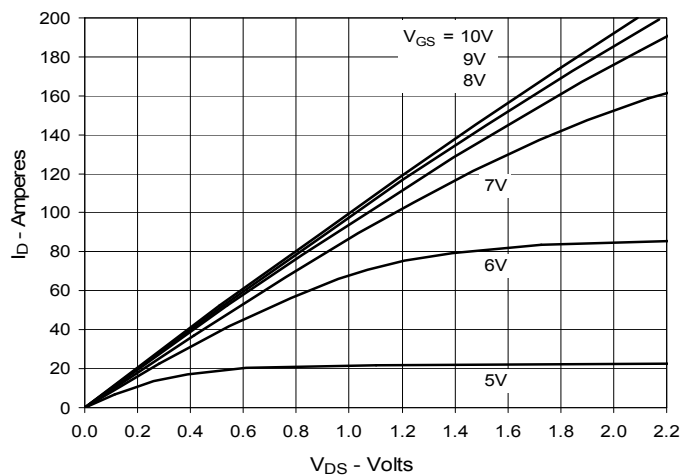
**Fig. 1. Output Characteristics
@ 25°C**



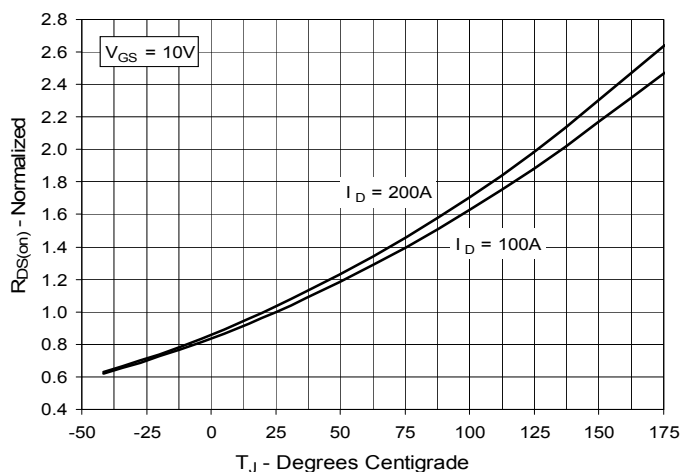
**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 100A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 100A$ Value
vs. Drain Current**

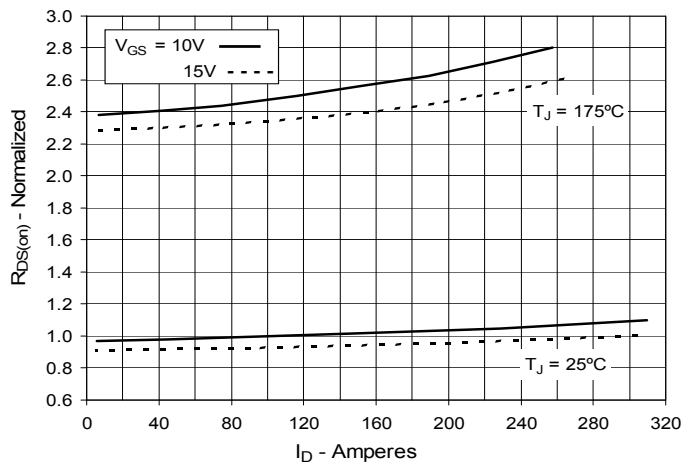


Fig. 6. Drain Current vs. Case Temperature

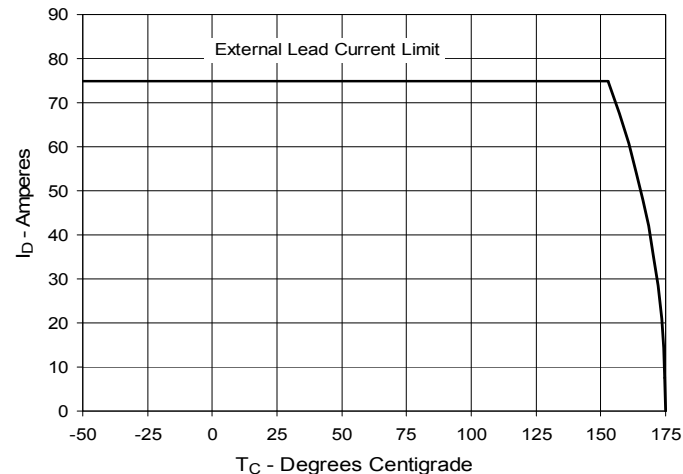


Fig. 7. Input Admittance

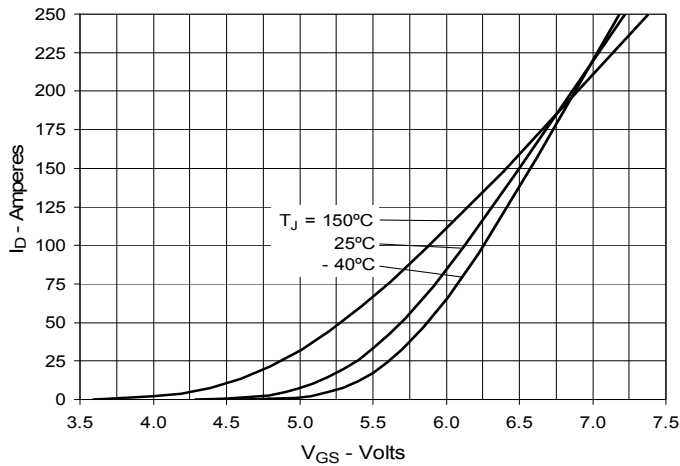


Fig. 8. Transconductance

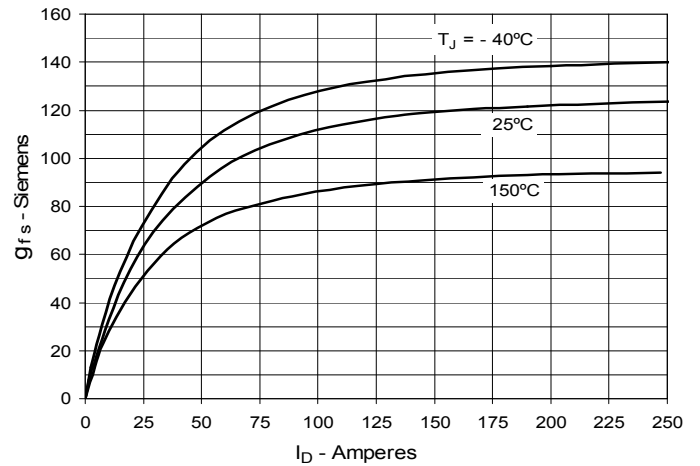


Fig. 9. Forward Voltage Drop of Intrinsic Diode

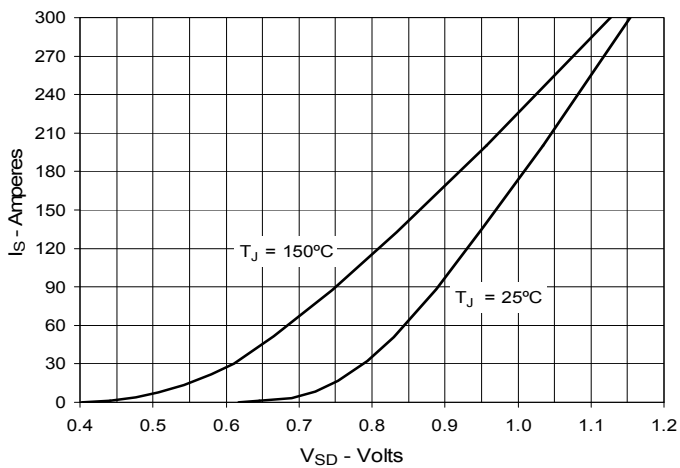


Fig. 10. Gate Charge

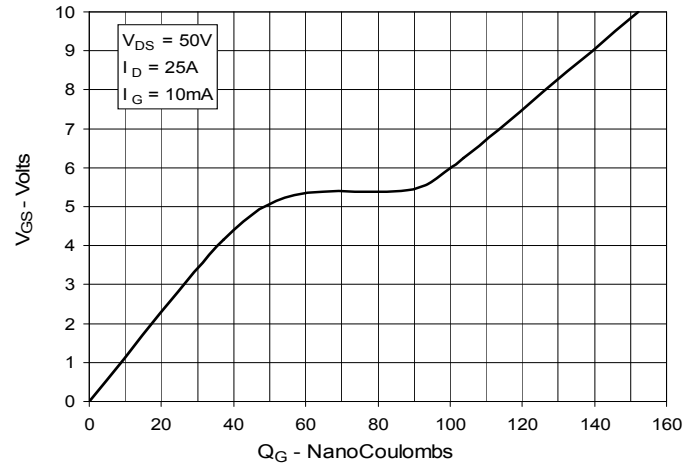


Fig. 11. Capacitance

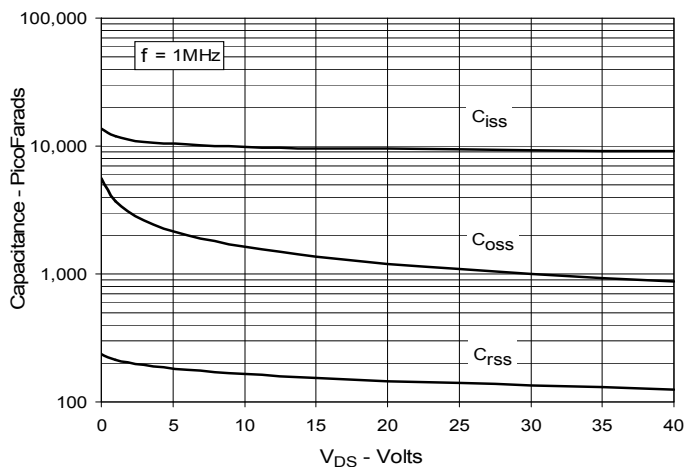
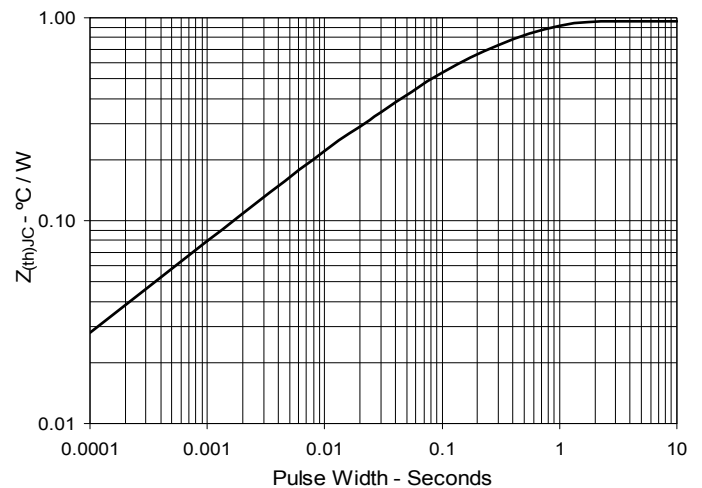
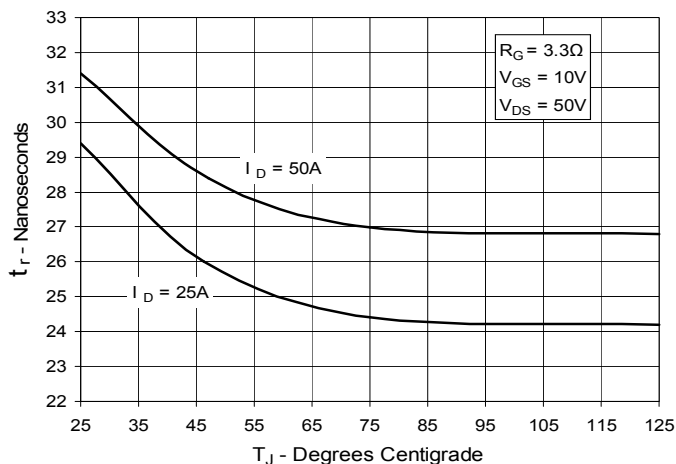


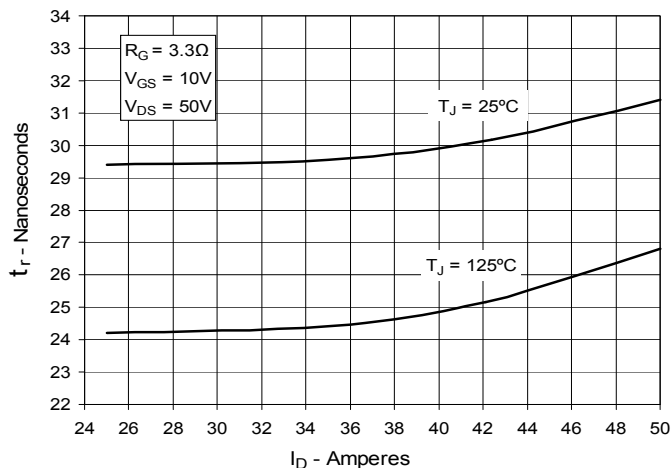
Fig. 12. Maximum Transient Thermal Impedance



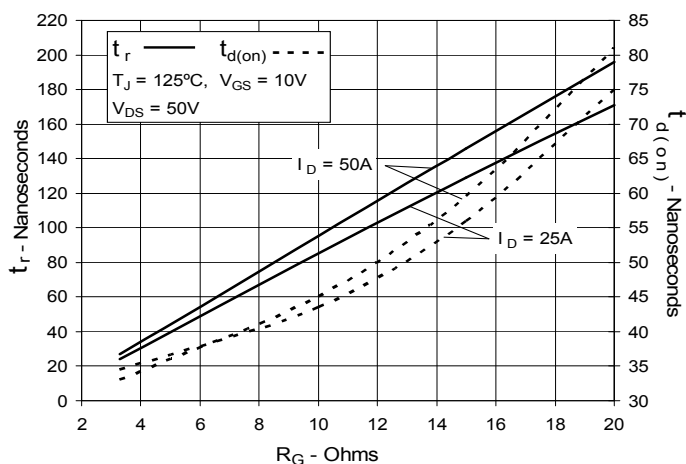
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



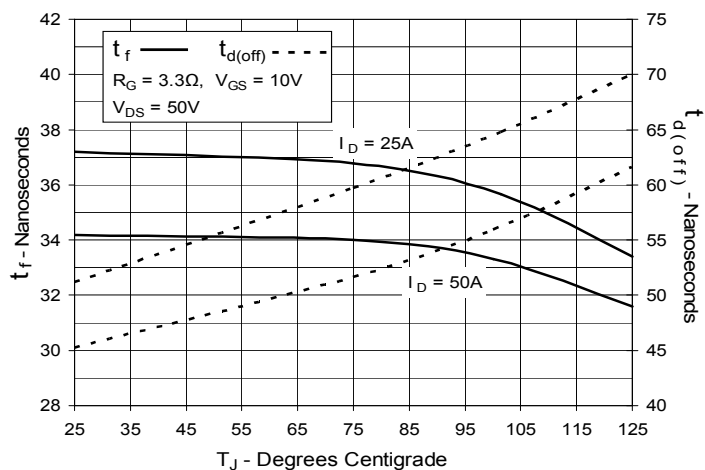
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



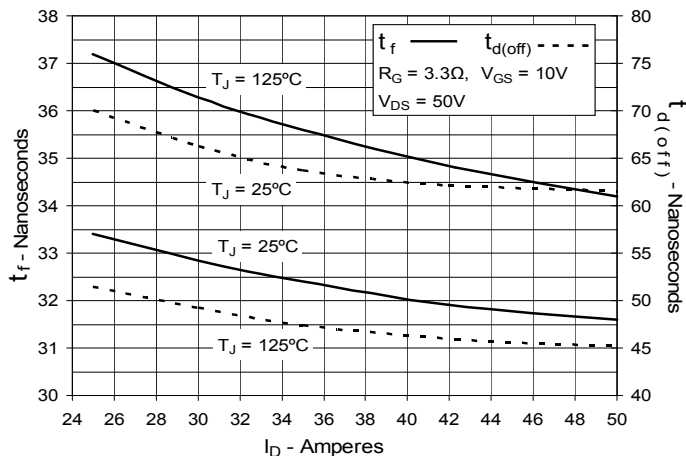
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**

